

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 1)
- ESD Protected Up To 2KV
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

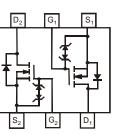
Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)









TOP VIEW

TOP VIEW



Maximum Ratings @T_A = 25°C unless otherwise specified

| Char | Symbol | Value | Unit | | |
|-----------------------------------|------------------|--|------------------|--------------|---|
| Drain-Source Voltage | V _{DSS} | 20 | V | | |
| Gate-Source Voltage | | | V _{GSS} | ±6 | V |
| Continuous Drain Current (Note 3) | Steady State | T _A = 25°C T _A = 85°C | ID | 1.38 0.89 | А |
| Pulsed Drain Current (Note 4) | I _{DM} | 3 | А | | |

Thermal Characteristics

| Characteristic | Symbol | Max | Unit |
|---|----------------------|-------------|------|
| Power Dissipation (Note 3) | PD | 530 | mW |
| Thermal Resistance, Junction to Ambient $@T_A = 25^{\circ}C$ (Note 3) | R _{θJA} | 235 | °C/W |
| Operating and Storage Temperature Range | TJ, T _{STG} | -55 to +150 | °C |

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

3. Device mounted on FR-4 PCB, with minimum recommended pad layout.

4. Repetitive rating, pulse width limited by junction temperature.

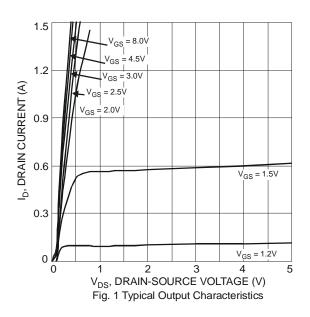


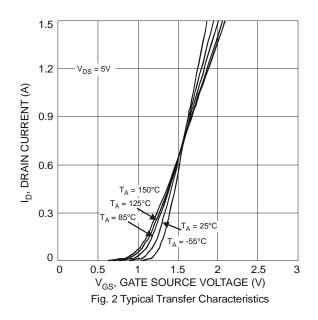
Electrical Characteristics @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|---|----------------------|-----|-------|------|------|--|
| OFF CHARACTERISTICS (Note 5) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 20 | - | - | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| Zero Gate Voltage Drain Current T _J = 25°C | I _{DSS} | - | - | 100 | nA | $V_{DS} = 20V, V_{GS} = 0V$ |
| Gate-Source Leakage | I _{GSS} | - | - | ±1.0 | μA | $V_{GS} = \pm 4.5 V, V_{DS} = 0 V$ |
| ON CHARACTERISTICS (Note 5) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | 0.5 | - | 1.0 | V | $V_{DS} = V_{GS}$, $I_D = 250 \mu A$ |
| | | | 0.3 | 0.45 | | $V_{GS} = 4.5V, I_D = 600mA$ |
| | | | 0.4 | 0.6 | | $V_{GS} = 2.5V, I_D = 500mA$ |
| Static Drain-Source On-Resistance | R _{DS (ON)} | - | 0.5 | 0.75 | Ω | $V_{GS} = 1.8V, I_D = 350mA$ |
| | | | - | 9 | | $V_{GS} = 1.7V, I_D = 140mA$ |
| | | | - | 10 | | $V_{GS} = 1.5V, I_D = 100mA$ |
| Forward Transfer Admittance | Y _{fs} | - | 1.4 | - | S | $V_{DS} = 10V, I_D = 400mA$ |
| Diode Forward Voltage | V _{SD} | | 0.7 | 1.2 | V | $V_{GS} = 0V, I_{S} = 150mA$ |
| DYNAMIC CHARACTERISTICS (Note 6) | | | | | | |
| Input Capacitance | C _{iss} | - | 60.67 | - | pF | |
| Output Capacitance | C _{oss} | - | 9.68 | - | pF | $V_{DS} = 16V, V_{GS} = 0V,$ f = 1.0MHz |
| Reverse Transfer Capacitance | C _{rss} | - | 5.37 | - | pF | 1 = 1.00012 |
| Total Gate Charge | Qg | - | 736.6 | - | рС | |
| Gate-Source Charge | Q _{gs} | - | 93.6 | - | рС | $V_{GS} = 4.5V, V_{DS} = 10V,$ |
| Gate-Drain Charge | Q _{gd} | - | 116.6 | - | рС | $I_D = 250 \text{mA}$ |
| Turn-On Delay Time | t _{D(on)} | - | 5.1 | - | ns | |
| Turn-On Rise Time | tr | - | 7.4 | - | ns | $V_{DD} = 10V, V_{GS} = 4.5V,$ |
| Turn-Off Delay Time | t _{D(off)} | - | 26.7 | - | ns | $R_{L} = 47\Omega, R_{G} = 10\Omega,$ $I_{D} = 200 \text{mA}$ |
| Turn-Off Fall Time | t _f | - | 12.3 | - | ns | |

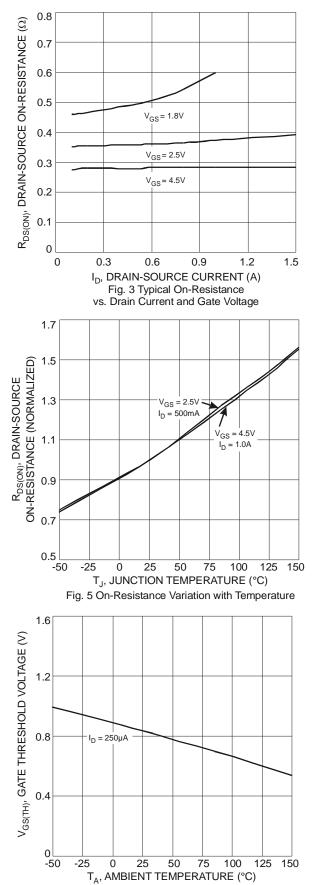
Notes: 5. Short duration pulse test used to minimize self-heating effect.

6. Guaranteed by design. Not subject to production testing.











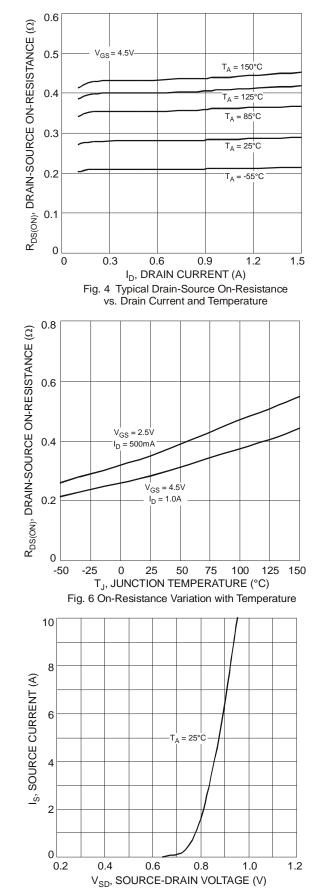
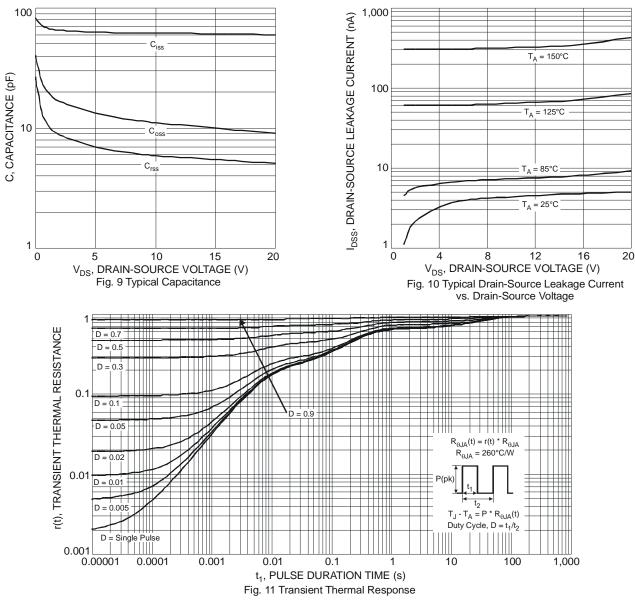


Fig. 8 Diode Forward Voltage vs. Current

NEW PRODUCT



DMG1024UV



Ordering Information (Note 7)

| Part Number | Case | Packaging |
|-------------|---------|--------------------|
| DMG1024UV-7 | SOT-563 | 3000 / Tape & Reel |

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

| [| | |] | Π | _ |
|---|---|----|---|---|---|
| | N | A1 | Y | М | |
| Т | Т | Т | | |] |

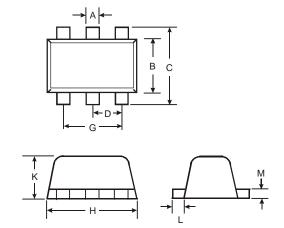
NA1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009)

M = Month (ex: 9 = September)

| Date Code Key | | | | | -4 | | | | | | | |
|---------------|------|-----|------|-----|------|-----|-----|------|-----|------|-----|------|
| Year | 2009 | Э | 2010 | | 2011 | 20 | 12 | 2013 | | 2014 | 1 | 2015 |
| Code | W | | Х | | Y | Z | Ζ | А | | В | | С |
| Month | Jan | Feb | Mar | Apr | Мау | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D |

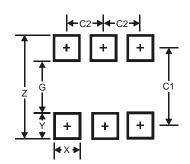


Package Outline Dimensions



| SOT-563 | | | | | | |
|---------|----------------------|------|------|--|--|--|
| Dim | Min | Max | Тур | | | |
| Α | 0.15 | 0.30 | 0.20 | | | |
| В | 1.10 | 1.25 | 1.20 | | | |
| С | 1.55 | 1.70 | 1.60 | | | |
| D | - | - | 0.50 | | | |
| G | 0.90 | 1.10 | 1.00 | | | |
| Н | 1.50 | 1.70 | 1.60 | | | |
| Κ | 0.55 | 0.60 | 0.60 | | | |
| L | 0.10 | 0.30 | 0.20 | | | |
| Μ | 0.10 | 0.18 | 0.11 | | | |
| All | All Dimensions in mm | | | | | |

Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 2.2 |
| G | 1.2 |
| Х | 0.375 |
| Y | 0.5 |
| C1 | 1.7 |
| C2 | 0.5 |



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